

Notice of References Cited

Application No.
08/757,112

Applicant(s)
Hisashi Ohtani

Examiner
Laura Schillinger

Group Art Unit
2813

Page 1 of 2

U.S. PATENT DOCUMENTS

| | DOCUMENT NO. | DATE | NAME | CLASS | SUBCLASS |
|---|--------------|----------|----------------|-------|----------|
| A | 5,147,826 | 9-15-92 | Liu et al | 438 | 233 |
| B | 5,529,937 | 6-25-96 | Zhang et al | 437 | 10 |
| C | 5,693,541 | 12-2-97 | Yamazaki et al | 437 | 21 |
| D | 5,569,610 | 10-29-96 | Zhang et al | 437 | 21 |
| E | | | | | |
| F | | | | | |
| G | | | | | |
| H | | | | | |
| I | | | | | |
| J | | | | | |
| K | | | | | |
| L | | | | | |
| M | | | | | |

16678 U.S. PTO
 09/379702
 08/24/99

FOREIGN PATENT DOCUMENTS

| | DOCUMENT NO. | DATE | COUNTRY | NAME | CLASS | SUBCLASS |
|---|--------------|------|---------|------|-------|----------|
| N | | | | | | |
| O | | | | | | |
| P | | | | | | |
| Q | | | | | | |
| R | | | | | | |
| S | | | | | | |
| T | | | | | | |

NON-PATENT DOCUMENTS

| | DOCUMENT (Including Author, Title, Source, and Pertinent Pages) | DATE |
|---|---|-------|
| U | Kawazu, Japanese Journal of Applied Physics: vol. 29 No.12 December 1990 pgs:2698-2704 "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation" | 12/90 |
| V | Kawazu, Japanese journal of Applied Physics: vol. 29 no.4 April 1990 pgs:729-738 "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon" | 4/90 |
| W | Hayzelden, Journal of Applied Physics: 73 (12), 15 June 1993 pgs:8279-8289 "Silicid Formation and Silicide-Mediated Crystallization of Nickel Implanted Amorphous Silicon Thin Films" | 6/93 |
| X | Kuo, The Electrochemical Society Proceedings: vol.94-35 pgs:116-122 "Thin Film Transistor Technologis" | 4/95 |

Notice of References CitedApplication No.
08/757,112Applicant(s)
Hlsashi OhtaniExaminer
Laura SchillingerGroup Art Unit
2813

Page 2 of 2

U.S. PATENT DOCUMENTS

| | DOCUMENT NO. | DATE | NAME | CLASS | SUBCLASS |
|---|--------------|------|------|-------|----------|
| A | | | | | |
| B | | | | | |
| C | | | | | |
| D | | | | | |
| E | | | | | |
| F | | | | | |
| G | | | | | |
| H | | | | | |
| I | | | | | |
| J | | | | | |
| K | | | | | |
| L | | | | | |
| M | | | | | |

FOREIGN PATENT DOCUMENTS

| | DOCUMENT NO. | DATE | COUNTRY | NAME | CLASS | SUBCLASS |
|---|--------------|------|---------|------|-------|----------|
| N | | | | | | |
| O | | | | | | |
| P | | | | | | |
| Q | | | | | | |
| R | | | | | | |
| S | | | | | | |
| T | | | | | | |

NON-PATENT DOCUMENTS

| | DOCUMENT (Including Author, Title, Source, and Pertinent Pages) | DATE |
|---|--|------|
| U | Liu, Applied Physics Letters 55 (7) 14 Aug.1989 pgs:660-662 "Selective area crystallization of amorphous silicon films by low-temperature rapid thermal annealing" | 8/89 |
| V | Cuane, Applied Surface Science 36 (1989) pgs:597-604 "Combined CW Laser and Furnace annealing of Amorphous Si and Ge in Contact With Some Metals" | 1/89 |
| W | Wolf, Silicon Processing for the VLSI Era , vol.2 1986 pgs:273-275 "Passivation Layers" | 1/86 |
| X | | |

Notice of References CitedApplication No.
08/757,112Applicant(s)
Ohtani et al.Examiner
Martin SulskyGroup Art Unit
2813

Page 1 of 1

U.S. PATENT DOCUMENTS

| | DOCUMENT NO. | DATE | NAME | CLASS | SUBCLASS |
|---|--------------|----------|-----------------|-------|----------|
| A | 5,744,824 | 6/2/95 | Kousai et al. | ---- | ---- |
| B | 5,621,224 | 10/5/95 | Yamazaki et al. | ---- | ---- |
| C | 5,817,549 | 8/30/95 | Yamazaki et al. | ---- | ---- |
| D | 5,773,846 | 5/24/95 | Zhang et al. | ---- | ---- |
| E | 5,756,364 | 11/22/95 | Tanaka et al. | ---- | ---- |
| F | | | | | |
| G | | | | | |
| H | | | | | |
| I | | | | | |
| J | | | | | |
| K | | | | | |
| L | | | | | |
| M | | | | | |

FOREIGN PATENT DOCUMENTS

| | DOCUMENT NO. | DATE | COUNTRY | NAME | CLASS | SUBCLASS |
|---|--------------|------|---------|------|-------|----------|
| N | | | | | | |
| | | | | | | |
| P | | | | | | |
| Q | | | | | | |
| R | | | | | | |
| S | | | | | | |
| T | | | | | | |

NON-PATENT DOCUMENTS

| | DOCUMENT (Including Author, Title, Source, and Pertinent Pages) | DATE |
|---|---|------|
| U | | |
| V | | |
| W | | |
| X | | |